

RQK2501YGDQA

Silicon N Channel MOS FET Power Switching

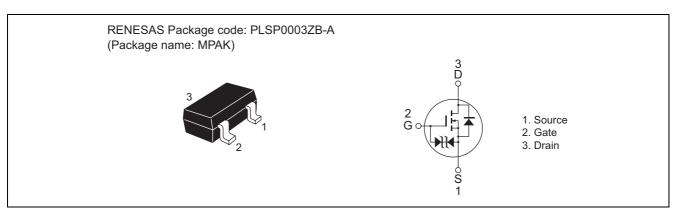
REJ03G1521-0200 Rev.2.00 Nov 06, 2007

Features

High drain to source voltage and Low gate drive
 V_{DSS}: 250 V and 2.5 V gate drive

- Low drive current
- High speed switching
- Small traditional package (MPAK)

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V_{DSS}	250	V	
Gate to source voltage	V_{GSS}	±10	V	
Drain current	I _D	0.4	A	
Drain peak current	I _{D(pulse)} Note1	1.6	A	
Body - drain diode reverse drain current	I _{DR}	0.4	A	
Channel dissipation	Pch Note2	0.8	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 μ s, Duty cycle \leq 1%

2. When using the glass epoxy board (FR-4 $40 \times 40 \times 1$ mm)

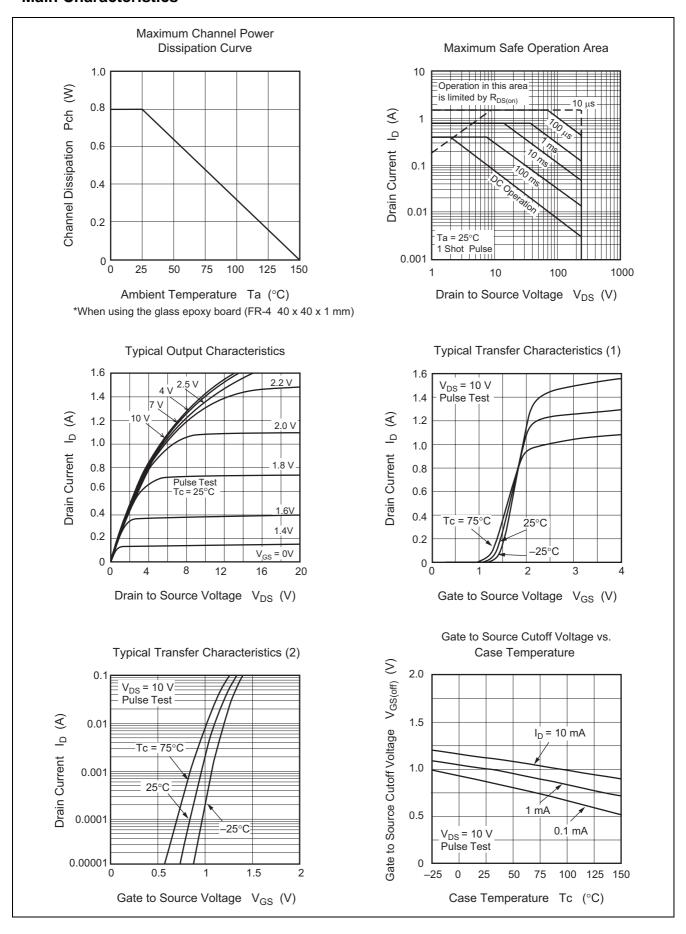
Electrical Characteristics

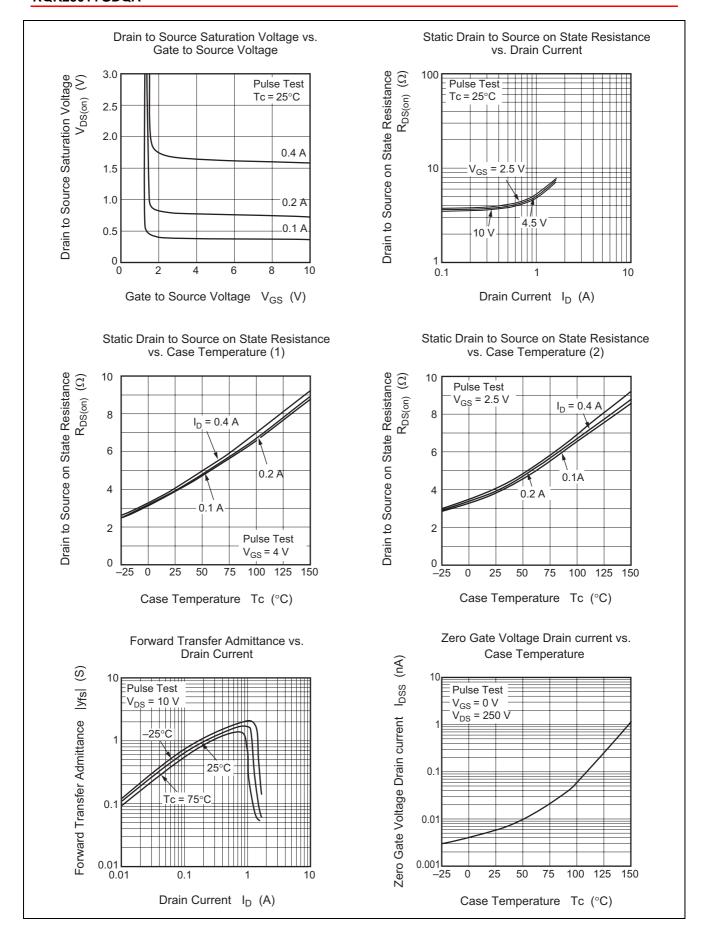
 $(Ta = 25^{\circ}C)$

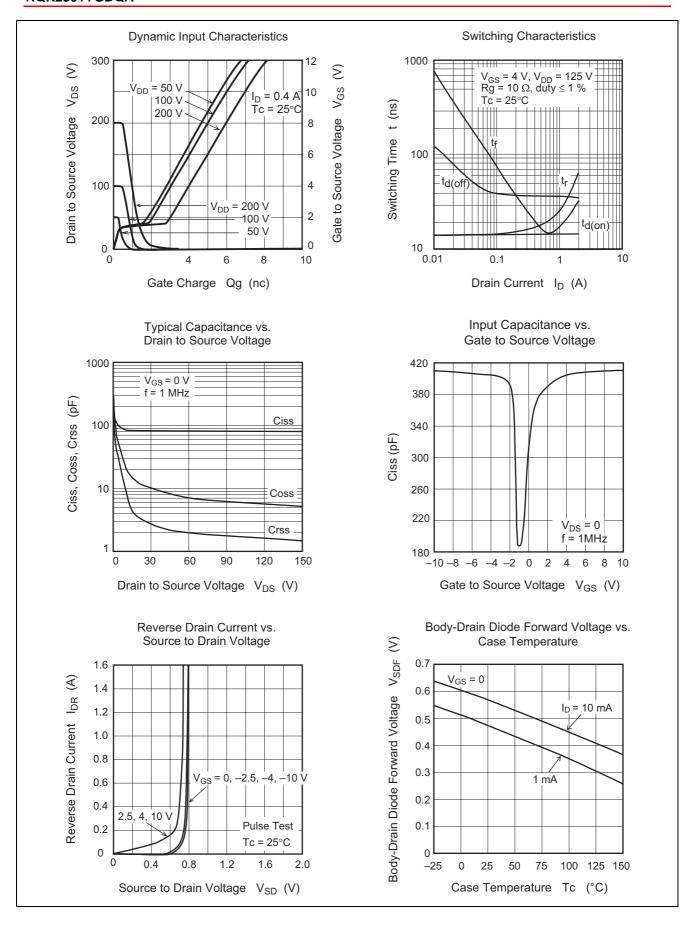
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	250	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	+10	_	_	V	$I_G = +100 \mu A, V_{DS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	-10	_	_	V	$I_G = -100 \ \mu A, \ V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_	_	+10	μΑ	$V_{GS} = +8 \text{ V}, V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_	_	-10	μΑ	$V_{GS} = -8 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 250 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	0.5	_	1.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	
Drain to source on state resistance	R _{DS(on)}	_	4.0	5.4	Ω	$I_D = 0.2 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note3}}$	
Drain to source on state resistance	R _{DS(on)}	_	4.1	5.6	Ω	$I_D = 0.2 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$	
Forward transfer admittance	y _{fs}	0.6	0.95	_	S	$I_D = 0.2 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$	
Input capacitance	Ciss	_	80	_	pF	V _{DS} = 25 V	
Output capacitance	Coss	_	10	_	pF	$V_{GS} = 0$	
Reverse transfer capacitance	Crss	_	3	_	pF	f = 1 MHz	
Turn - on delay time	t _{d(on)}	_	15	_	ns	V _{DD} = 125 V,V _{GS} = 4 V	
Rise time	t _r	_	16	_	ns	$I_D = 0.2 \text{ A}$	
Turn - off delay time	t _{d(off)}	_	40	_	ns	$R_L = 625 \Omega$	
Fall time	t _f	_	38	_	ns	$Rg = 10 \Omega$	
Total gate charge	Qg	_	4.0	_	nC	V _{DD} = 200 V	
Gate to Source charge	Qgs	_	0.5	_	nC	$V_{GS} = 4 V$	
Gate to drain charge	Qgd	_	2.6	_	nC	$I_D = 0.4 A$	
Body - drain diode forward voltage	V_{DF}	_	0.8	1.2	V	$I_F = 0.4 \text{ A}, V_{GS} = 0^{\text{Note3}}$	

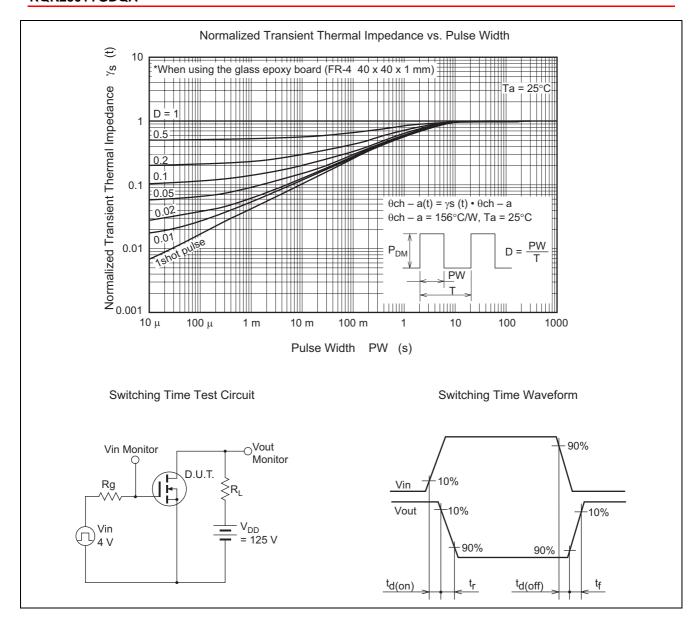
Notes: 3. Pulse test

Main Characteristics

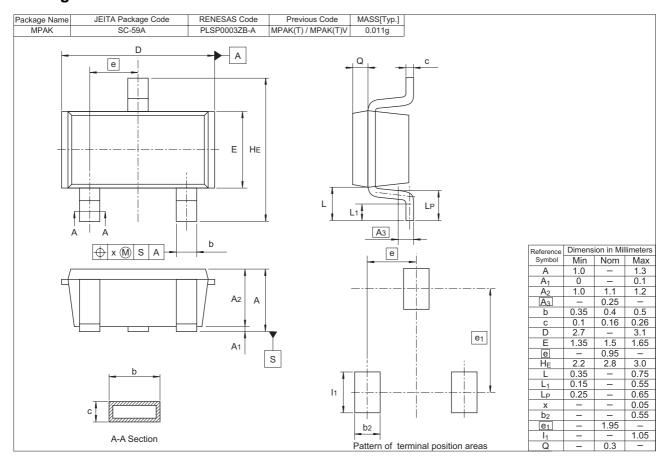








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RQK2501YGDQATL-E	3000 pcs.	φ178 mm reel, 8 mm Emboss taping

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